

~~INFORMATION DISCLOSURE~~  
~~CITATION TYPE~~

ATTY. DOCKET NO.

**SERIAL NO.**

**340-80**

**10/686,520**

**APPLICANT**

KOCHERGIN et al.

FILING DATE

**TC/A.U.**

**16 October 2003**

2883

**U.S. PATENT DOCUMENTS**

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS** (including Author, Title, Date, Pertinent pages, etc.)

[illegible]

• Examiner

Chris Kalwoch

**Date Considered**

7-28-05

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## U.S. PATENT DOCUMENTS

INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Conf	4,874,484	10/1989	Foell et al.	438	750	
A	5,262,021	11/1993	V. Lehmann et al.	265	655	
	5,348,627	09/1994	Propst et al.	205	655	
	5,431,766	07/1995	Propst et al.	156	345.15	
	5,544,772	08/1996	Soave et al.	216	2	
	5,645,684	07/1997	Keller	148	33.2	
	5,987,208	11/1999	Grunig	385	148	
	5,997,713	12/1999	Beetz, Jr. et al.	205	124	
	6,521,149	02/2003	Mearini et al.	264	81	
Conf	6,526,191	02/2003	Geusic et al.	385	14	

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DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
3717851		Germany			
Conf 4202454		Germany			

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Conf	Lehmann et al., Optical shortpass filters based on macroporous silicon <i>Appl. Phys. Lett.</i> V 78, N.5, Jan. 2001.
Conf	J. Schilling et al., "Three-dimensional photonic crystals based on Macroporous silicon with modulated pore diameter", <i>Appl. Phys. Lett.</i> V 78, N.9, Feb. 2001
Conf	S. Izuo et al., "A novel electrochemical etching technique for n-type silicon," <i>Sensors and Actuators A</i> 97-98 (2002), pp. 720-724
Conf	A. Vyatkin et al., "Random and Ordered Macropore Formation in p-Type Silicon," <i>J. of the Electrochem. Soc.</i> , 149 (1), pp. G70-G76 (2002)
	H. Föll et. al, "Formation and application of porous silicon", <i>Mat. Sci. Eng. R</i> 39 (2002), pp. 93-141

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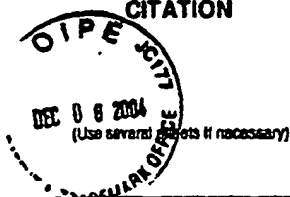
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**U.S. PATENT DOCUMENTS**

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## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent pages, etc.)

[illegible]

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**TC/A.U.**

16 October 2003

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**U.S. PATENT DOCUMENTS**

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent pages, etc.)**

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Chris Kellogg

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1-18-05

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	H. H. Föll et al., "Porous III-V compound semiconductors: formation, properties, and comparison to silicon", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 61-70 (2003)
out	M. Christophersen et al., "A comparison of pores in silicon and pores in III-V compound materials", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 197-203, (2003)
out	H. Föll et al., "Pores in III-V Semiconductors", <i>Adv. Materials, Review</i> , 2003, 15, pp.183 - 198, (2003)
out	S. Langa et al., <i>Phys. Stat. Sol. A</i> , 197 (1), p. 77, (2003) "Single crystalline 2D porous arrays obtained by self organization in n-InP" (pp. 77-82)
out	K. Barla et al., "X-Ray Topographic Characterization of Porous Silicon Layers," <i>J. Cryst. Growth</i> , 68, North-Holland, Amsterdam, p. 721-726 (1984)
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out	P.A. Kohl et al., <i>J. Electrochem. Soc.</i> , 130, p. 2288 (1983)
out	Schmuki P. et al., <i>Physica Status Solidi A</i> , "Pore Formation on n-InP," 182 (1), pp. 51-61, (2000)
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\*Examiner

Ch. Kalish

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